



April 5, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/796,893 03/09/04 |
| Lap Chan et al.

| A NEW METHOD TO FORM A CROSS NETWORK
OF AIR GAPS WITHIN IMD LAYER

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on April 12, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

S. B. A. 4/12/04

U.S. Patent 5,828,121 to Lur et al., "Multi-Level Conduction Structure for VLSI Circuits," describes an air gap between metal lines at different levels by etching the dielectric layers between the metal line levels.

U.S. Patent 5,783,864 to Dawson et al., "Multilevel Interconnect Structure of an Integrated Circuit having Air Gaps and Pillars Separating Levels of Interconnect," describes air gaps and pillars between metal layers.

U.S. Patent 5,561,085 to Gorowitz et al., "Structure of Protecting Air Bridges on Semiconductor Chips from Damage," describes a method for forming air gap bridges.

The following two U.S. Patents describe air gap processes:

- 1) U.S. Patent 5,461,003 to Havemann et al., "Multilevel Interconnect Structure with Air Gaps Formed Between Metal Leads."
- 2) U.S. Patent 5,527,737 to Jeng, "Selective Formation of Low-Density, Low-Dielectric-Constant Insulators in Narrow Gaps for Line-To-Line Capacitance Reduction."

CS-99-120B

U.S. Patent 5,908,318 to Wang et al., "Method of Forming Low Capacitance Interconnect Structures on Semiconducor Substrates," describes an air gap in an ILD by etch out.

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.